

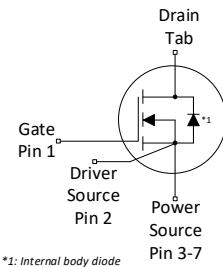
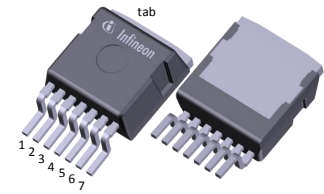
CoolSiC™

PG-T0263-7

400V CoolSiC™ G2 MOSFET

Features

- Ideal for high frequency switching and synchronous rectification
- Commutation robust fast body diode with low Q_{fr}
- Low $R_{DS(on)}$ dependency on temperature
- Benchmark gate threshold voltage, $V_{GS(th)} = 4.5\text{ V}$
- Recommended gate driving voltage 0 V to 18 V
- .XT interconnection technology for best-in-class thermal performance
- 100% avalanche tested



Potential applications

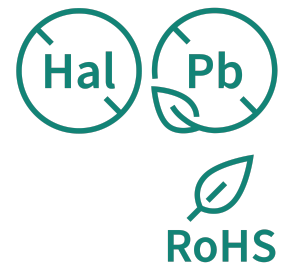
- SMPS
- Solar PV inverters
- Energy storage, UPS and battery formation
- Class-D audio
- Motor drives

Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	400	V
$R_{DS(on),typ}$	25.4	mΩ
I_D	68	A
Q_{oss}	59	nC
E_{oss}	4.2	μJ
Q_G	36	nC



Type/Ordering Code	Package	Marking	Related Links
IMBG40R025M2H	PG-T0263-7	40R025M2	-



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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	68 48 9	A	$V_{GS}=18\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=18\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=18\text{ V}$, $T_A=25\text{ °C}$, $R_{THJA}=40\text{ °C/W}^2)$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	204	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	93	mJ	$I_D=15.7\text{ A}$, $R_{GS}=25\text{ }\Omega$
Avalanche energy, repetitive	E_{AR}	-	-	0.47	mJ	$I_D=15.7\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage (static)	$V_{GS,DC}$	-7	-	23	V	-
Gate source voltage (transient)	$V_{GS,AC}$	-10	-	25	V	$t_{pulse} \leq 500\text{ ns}$, duty cycle $\leq 1\%$
Power dissipation	P_{tot}	-	-	214 3.8	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{THJA}=40\text{ °C/W}^2)$
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature	T_j	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagram 3 for more detailed information.

⁴⁾ See Diagram 19 for more detailed information.

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.7	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}	-	-	40	°C/W	-

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

3 Operating range

Table 4 Operating range

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Recommended turn-on voltage	$V_{GS(on)}$	-	18	-	V	-
Recommended turn-off voltage	$V_{GS(off)}$	-	0	-	V	-

4 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 5 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	400	-	-	V	$V_{GS}=0\text{ V}$, $I_D=0.56\text{ mA}$
Gate threshold voltage ⁶⁾	$V_{GS(th)}$	3.5	4.5	5.6	V	$V_{DS}=V_{GS}$, $I_D=5.6\text{ mA}$
Zero gate voltage drain current	I_{DSS}	-	1 2	75 -	μA	$V_{DS}=400\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=400\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=175\text{ °C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	25.4 36.5 31.1	32.1 - -	m Ω	$V_{GS}=18\text{ V}$, $I_D=15.7\text{ A}$, $T_j=25\text{ °C}$ $V_{GS}=18\text{ V}$, $I_D=15.7\text{ A}$, $T_j=175\text{ °C}$ $V_{GS}=15\text{ V}$, $I_D=15.7\text{ A}$, $T_j=25\text{ °C}$
Gate resistance	R_G	-	3.3	5.0	Ω	-

⁶⁾ Tested after 1ms pulse at $V_{GS} = +20\text{V}$.

Table 6 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	1200	1690	pF	$V_{GS}=0\text{ V}$, $V_{DS}=200\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	180	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=200\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	14	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=200\text{ V}$, $f=1\text{ MHz}$
Effective output capacitance, energy related ⁷⁾	$C_{o(er)}$	-	211	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=0\dots200\text{ V}$
Effective output capacitance, time related ⁸⁾	$C_{o(tr)}$	-	290	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{ V}$, $V_{DS}=0\dots200\text{ V}$
Turn-on delay time ⁹⁾	$t_{d(on)}$	-	12.5	-	ns	$V_{DD}=200\text{ V}$, $V_{GS}=0\dots18\text{ V}$, $I_D=15.7\text{ A}$, $R_{G,ext}=1.8\text{ }\Omega$
Rise time ⁹⁾	t_r	-	11.9	-	ns	$V_{DD}=200\text{ V}$, $V_{GS}=0\dots18\text{ V}$, $I_D=15.7\text{ A}$, $R_{G,ext}=1.8\text{ }\Omega$
Turn-off delay time ⁹⁾	$t_{d(off)}$	-	19.9	-	ns	$V_{DD}=200\text{ V}$, $V_{GS}=18\dots0\text{ V}$, $I_D=15.7\text{ A}$, $R_{G,ext}=1.8\text{ }\Omega$
Fall time ⁹⁾	t_f	-	7.9	-	ns	$V_{DD}=200\text{ V}$, $V_{GS}=18\dots0\text{ V}$, $I_D=15.7\text{ A}$, $R_{G,ext}=1.8\text{ }\Omega$

⁷⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 200 V.

⁸⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 200 V.

⁹⁾ Refer to Table 9 for test setup.

Table 7 Gate Charge Characteristics ¹⁰⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	9.8	-	nC	$V_{DD}=200\text{ V}$, $I_D=15.7\text{ A}$, $V_{GS}=0\text{ to }18\text{ V}$
Gate to drain charge	Q_{gd}	-	7.5	-	nC	$V_{DD}=200\text{ V}$, $I_D=15.7\text{ A}$, $V_{GS}=0\text{ to }18\text{ V}$
Gate charge total	Q_g	-	36	-	nC	$V_{DD}=200\text{ V}$, $I_D=15.7\text{ A}$, $V_{GS}=0\text{ to }18\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	34	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }18\text{ V}$
Output charge	Q_{oss}	-	59	-	nC	$V_{DS}=200\text{ V}$, $V_{GS}=0\text{ V}$
Output Energy	E_{oss}	-	4.2	-	μJ	$V_{DS}=200\text{ V}$, $V_{GS}=0\text{ V}$

¹⁰⁾ As per JEP192, Guidelines for Gate Charge (Q_g) Test Method for SiC MOSFET.

Table 8 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	32	A	$T_c=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	204	A	$T_c=25\text{ °C}$, $t_{pulse}\leq 250\text{ ns}$
Diode forward voltage	V_{SD}	-	3.5	4.3	V	$V_{GS}=0\text{ V}$, $I_S=15.7\text{ A}$, $T_j=25\text{ °C}$
MOSFET forward recovery time	t_{fr}	-	13.6 8.9	-	ns	$V_R=200\text{ V}$, $I_S=15.7\text{ A}$, $di_S/dt=1000\text{ A}/\mu\text{s}$ $V_R=200\text{ V}$, $I_S=15.7\text{ A}$, $di_S/dt=4000\text{ A}/\mu\text{s}$
MOSFET forward recovery charge ¹¹⁾	Q_{fr}	-	55 116	-	nC	$V_R=200\text{ V}$, $I_S=15.7\text{ A}$, $di_S/dt=1000\text{ A}/\mu\text{s}$ $V_R=200\text{ V}$, $I_S=15.7\text{ A}$, $di_S/dt=4000\text{ A}/\mu\text{s}$

¹¹⁾ Q_{fr} includes Q_{oss} . Refer to Table 10 for test setup.

5 Electrical characteristics diagrams

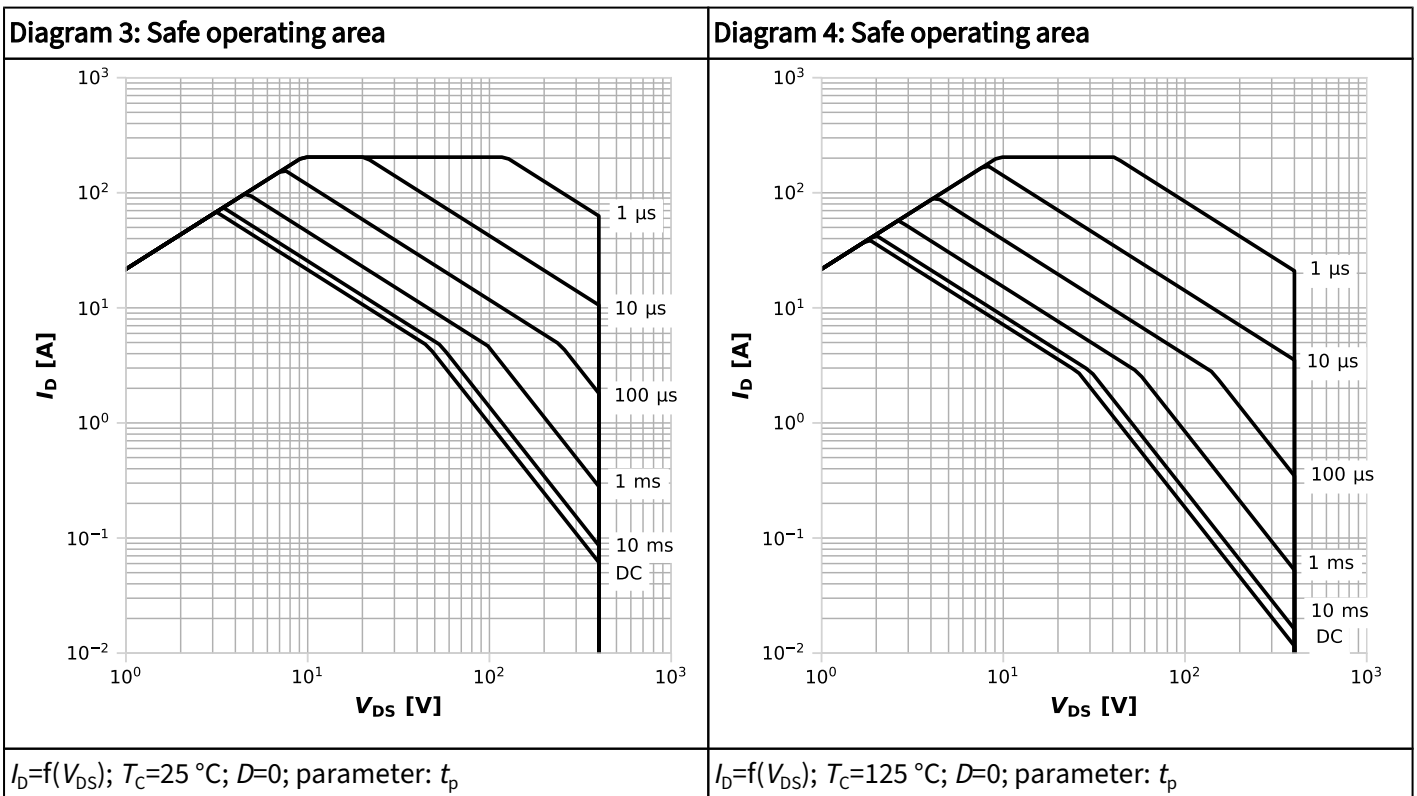
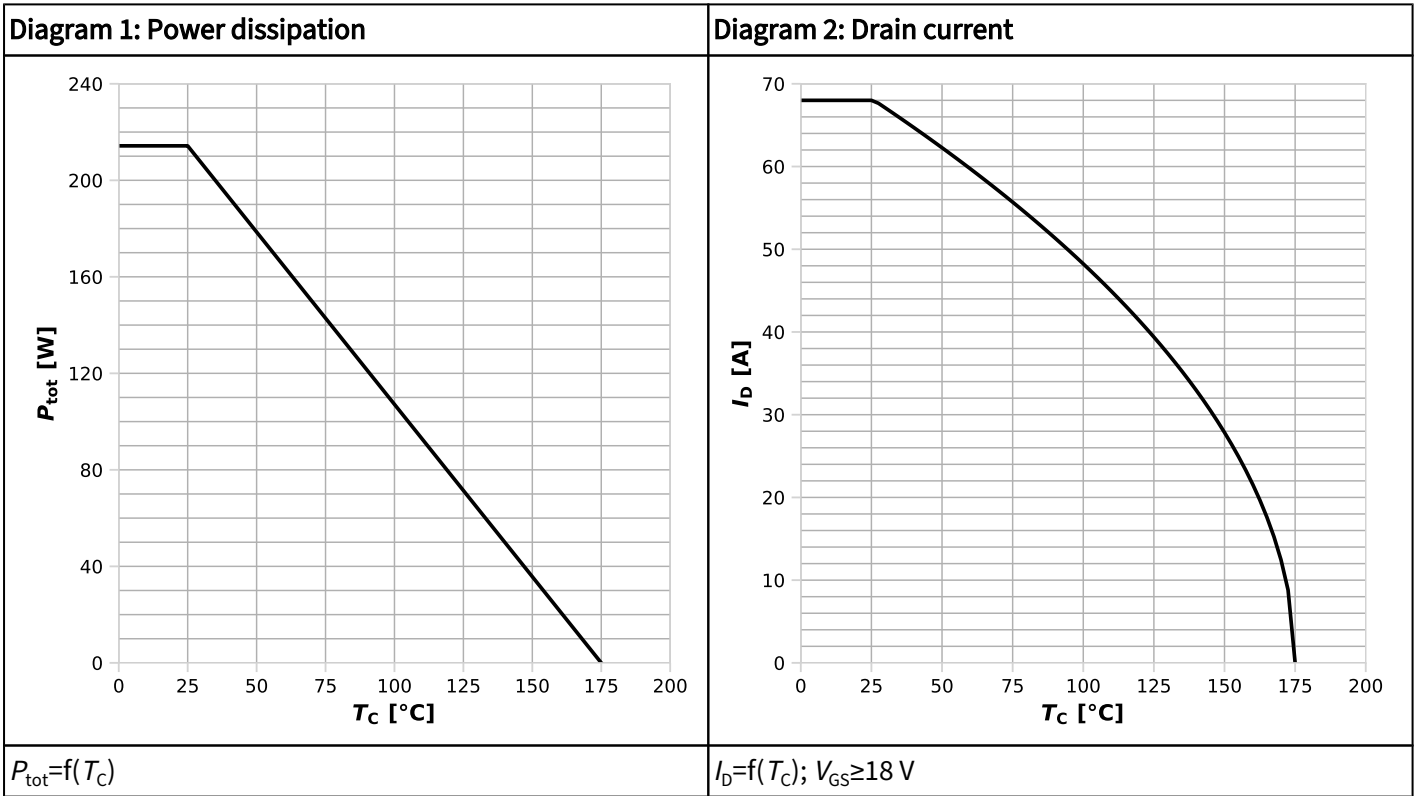
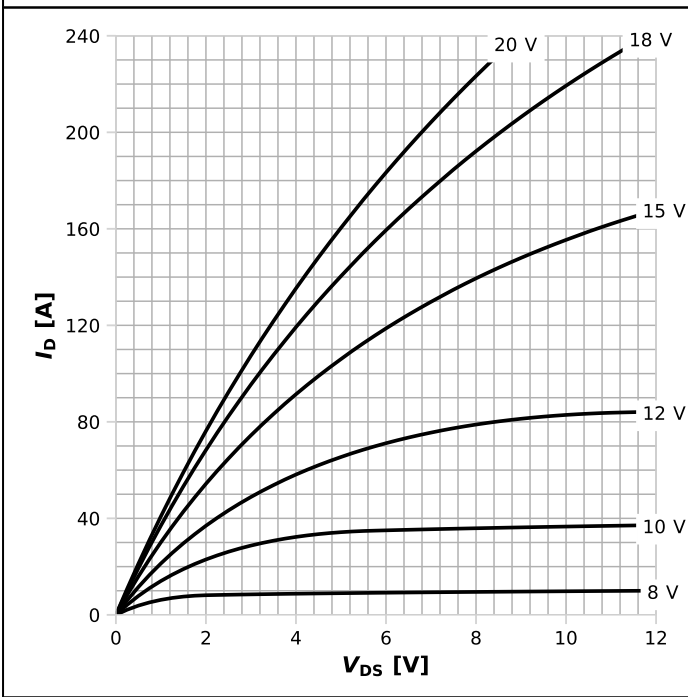
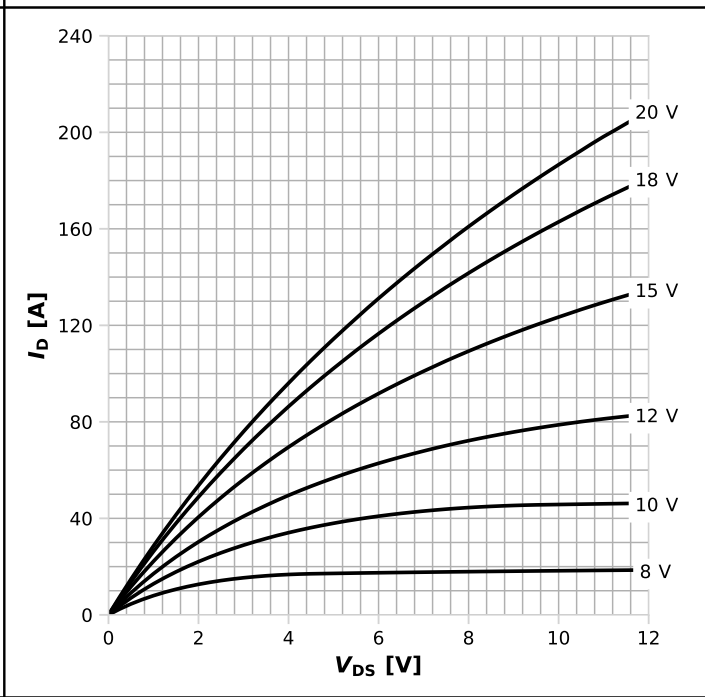


Diagram 5: Typ. output characteristics



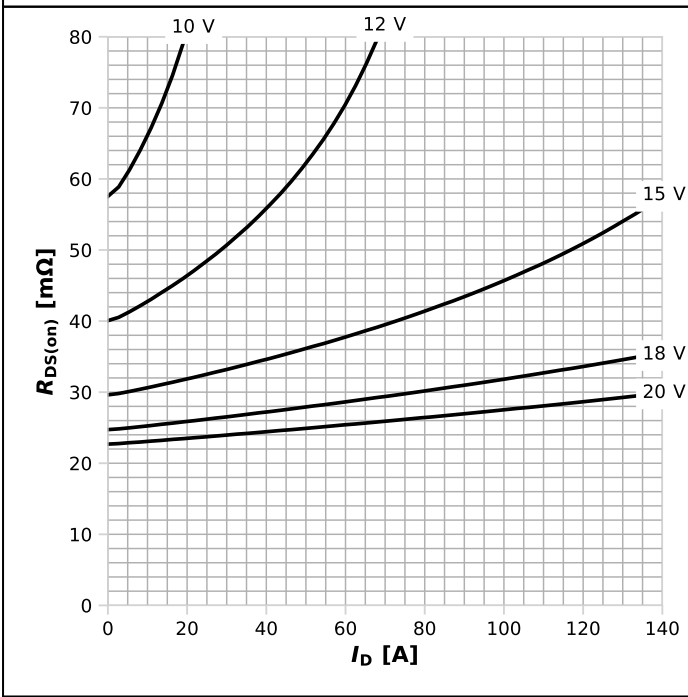
$I_D = f(V_{DS})$, $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



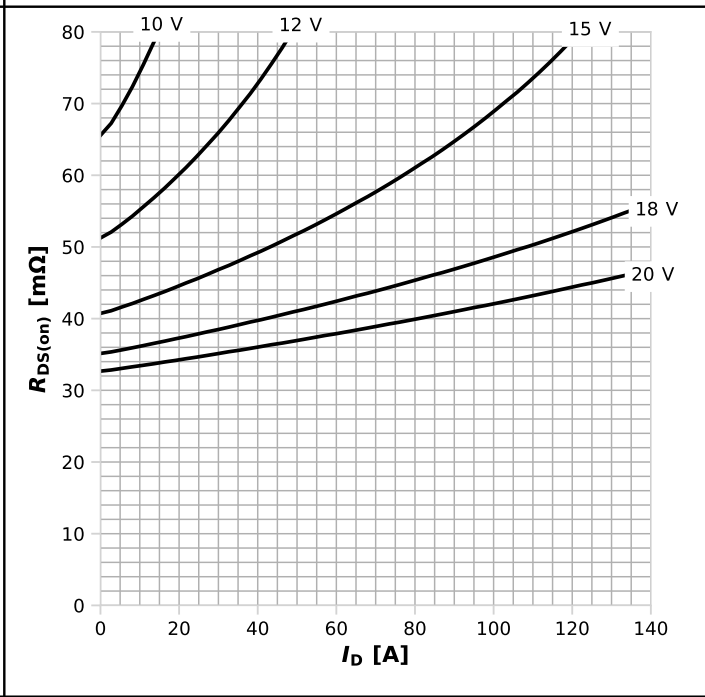
$I_D = f(V_{DS})$, $T_j = 175\text{ °C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on resistance



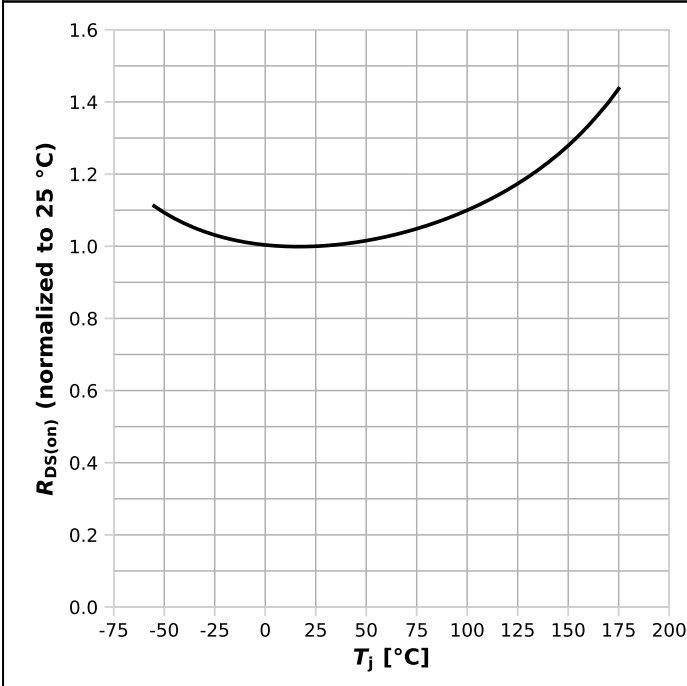
$R_{DS(on)} = f(I_D)$, $T_j = 25\text{ °C}$; parameter: V_{GS}

Diagram 8: Typ. drain-source on resistance



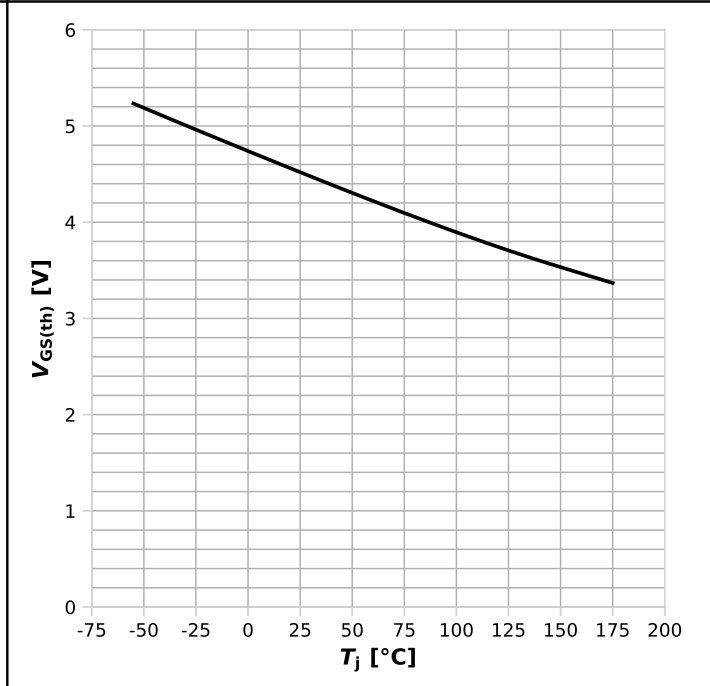
$R_{DS(on)} = f(I_D)$, $T_j = 175\text{ °C}$; parameter: V_{GS}

Diagram 9: Normalized drain-source on resistance



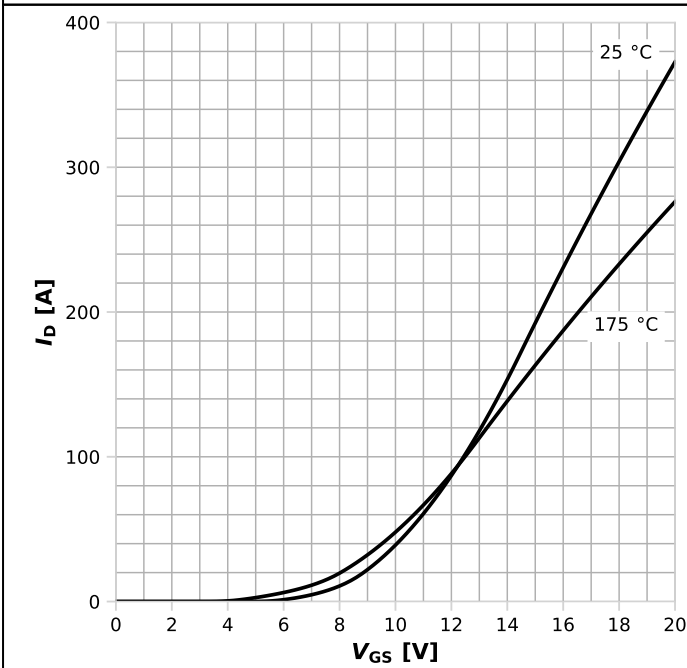
$R_{DS(on)}=f(T_j), I_D=15.7 \text{ A}, V_{GS}=18 \text{ V}$

Diagram 10: Typ. gate threshold voltage



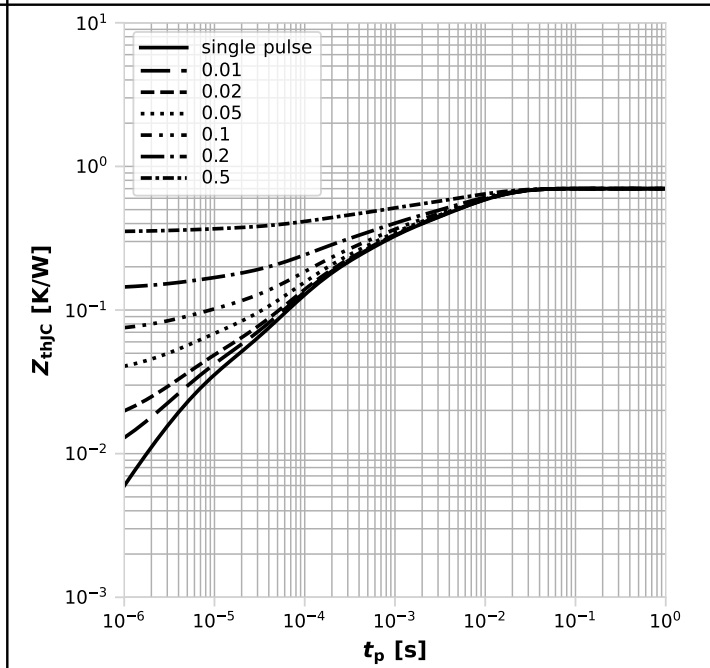
$V_{GS(th)}=f(T_j), V_{GS}=V_{DS}, I_D=5.6 \text{ mA}$

Diagram 11: Typ. transfer characteristics



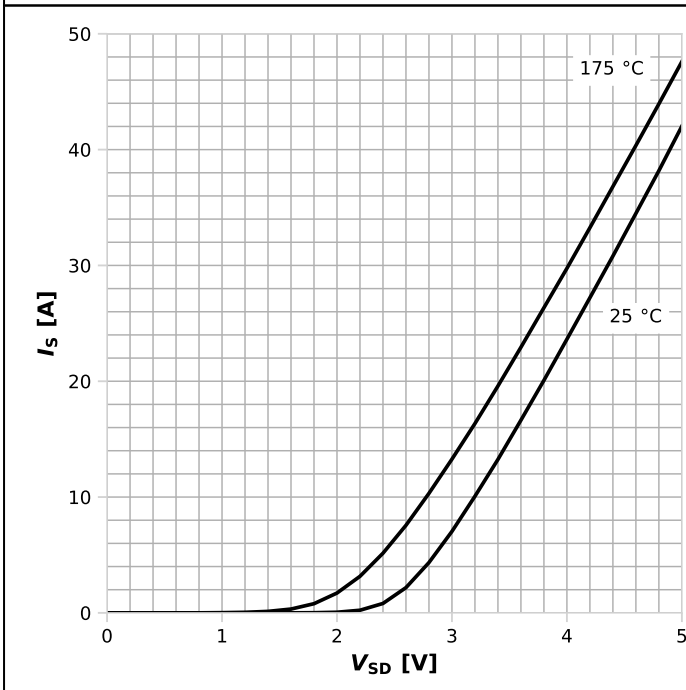
$I_D=f(V_{GS}), |V_{DS}|>2|I_D|R_{DS(on)max}; \text{ parameter: } T_j$

Diagram 12: Max. transient thermal impedance



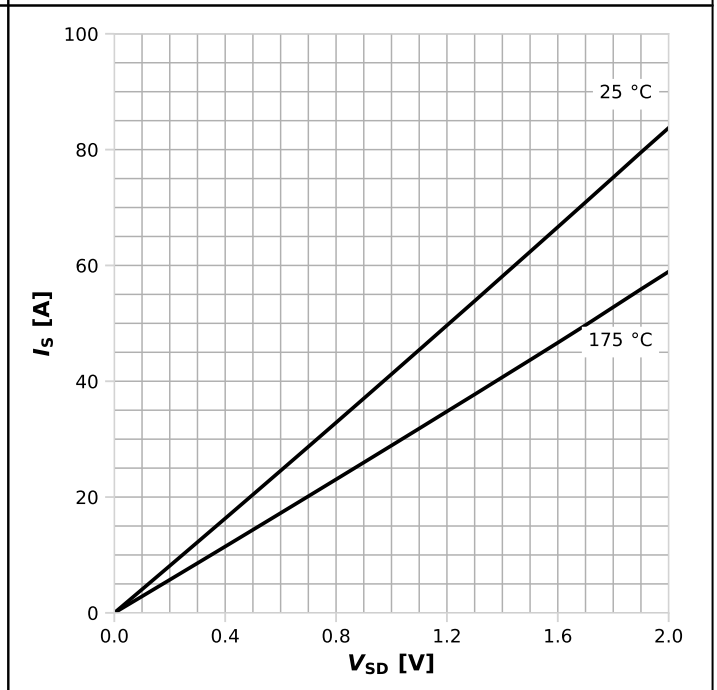
$Z_{thJC}=f(t_p); \text{ parameter: } D=t_p/T$

Diagram 13: Reverse output characteristics



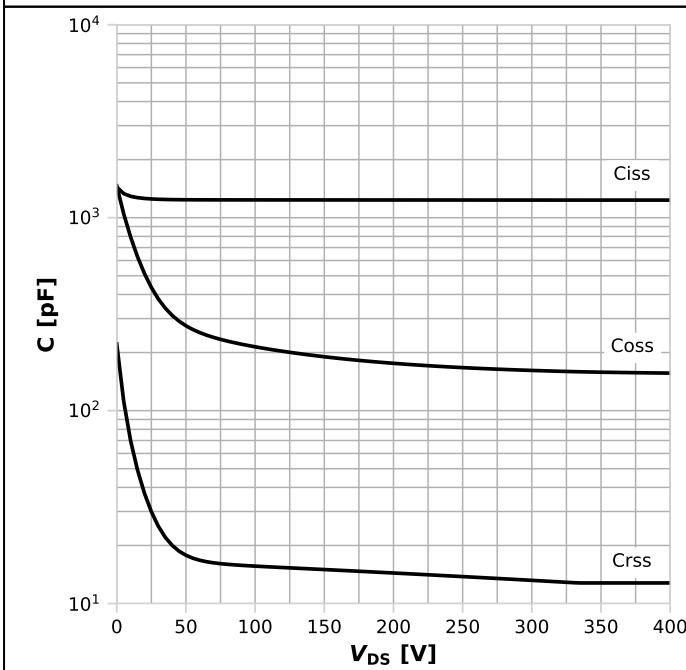
$I_F = f(V_{SD}), V_{GS} = 0 \text{ V}; \text{ parameter: } T_j$

Diagram 14: Reverse output characteristics



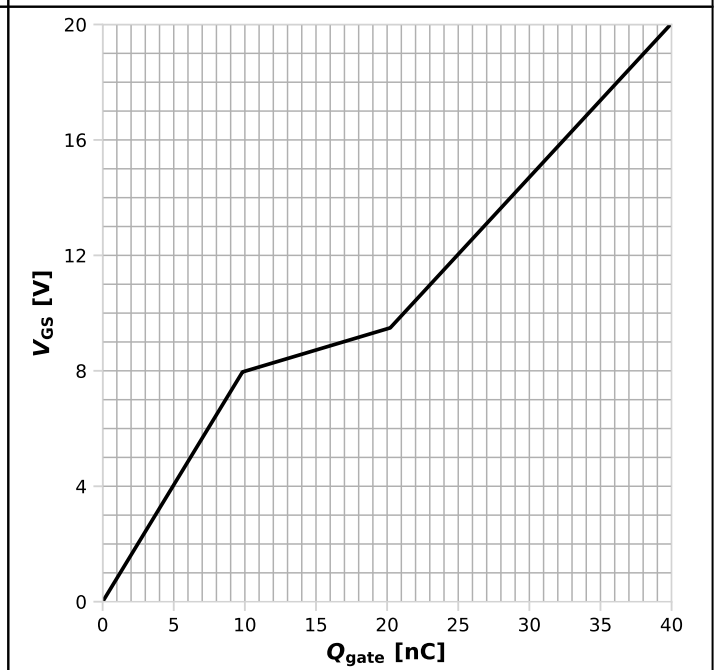
$I_F = f(V_{SD}), V_{GS} = 18 \text{ V}; \text{ parameter: } T_j$

Diagram 15: Typ. capacitances

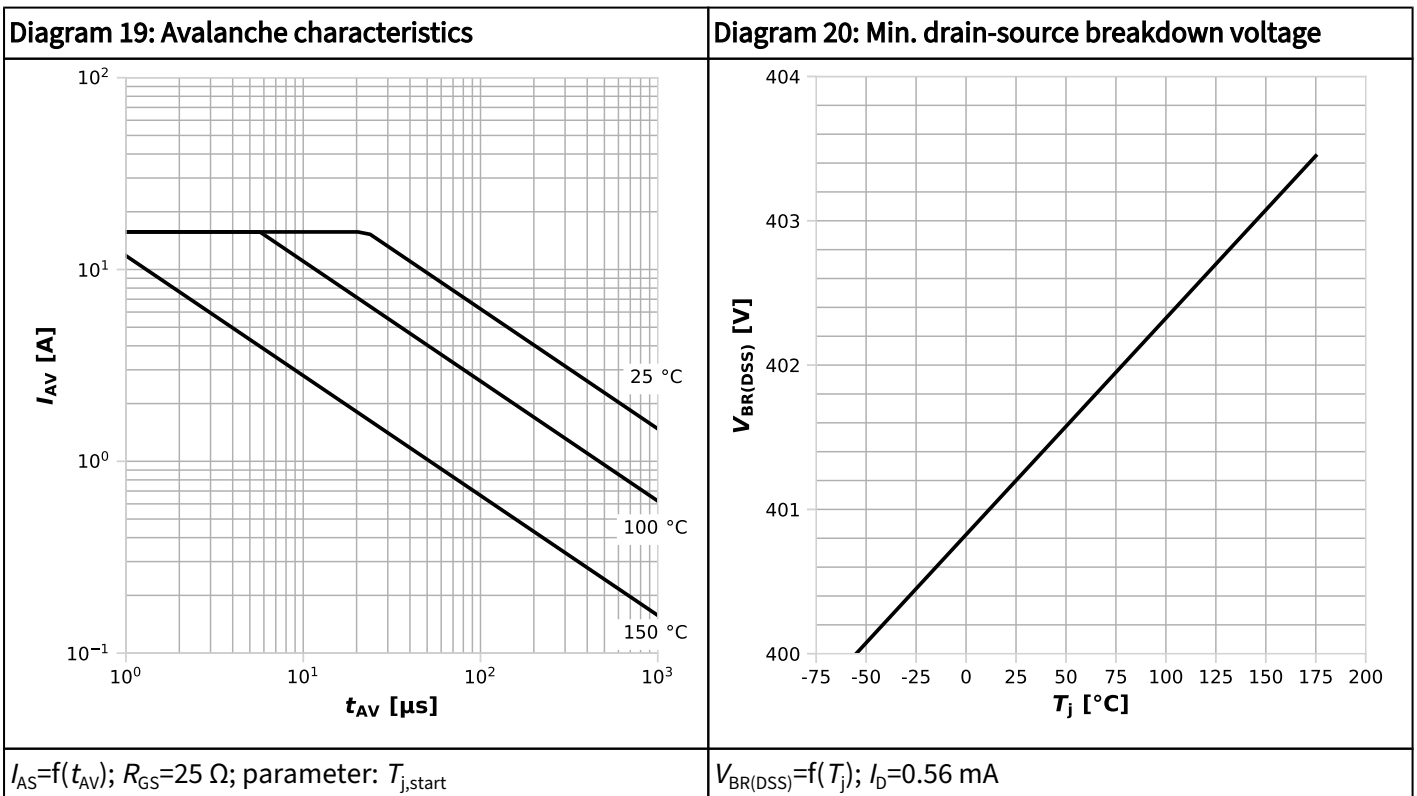
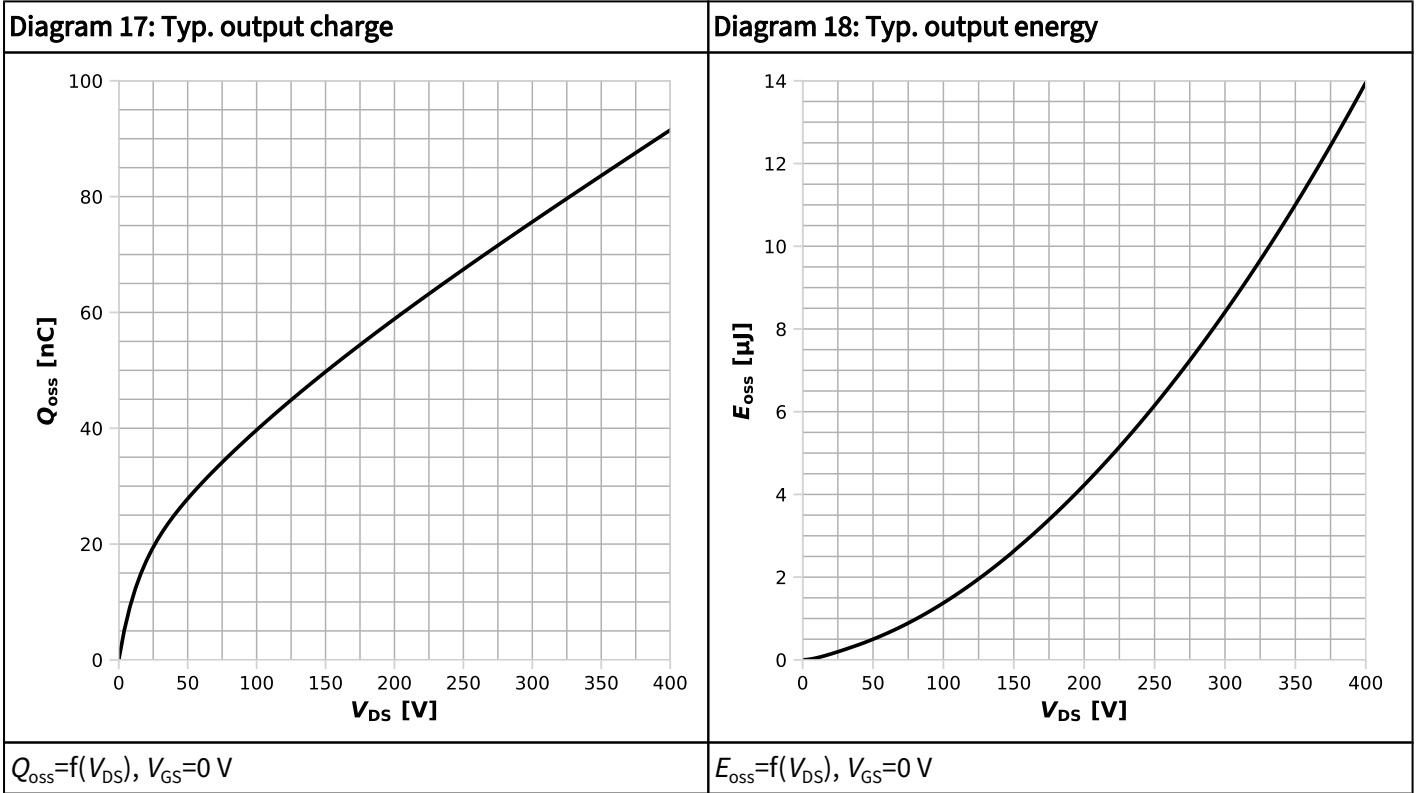


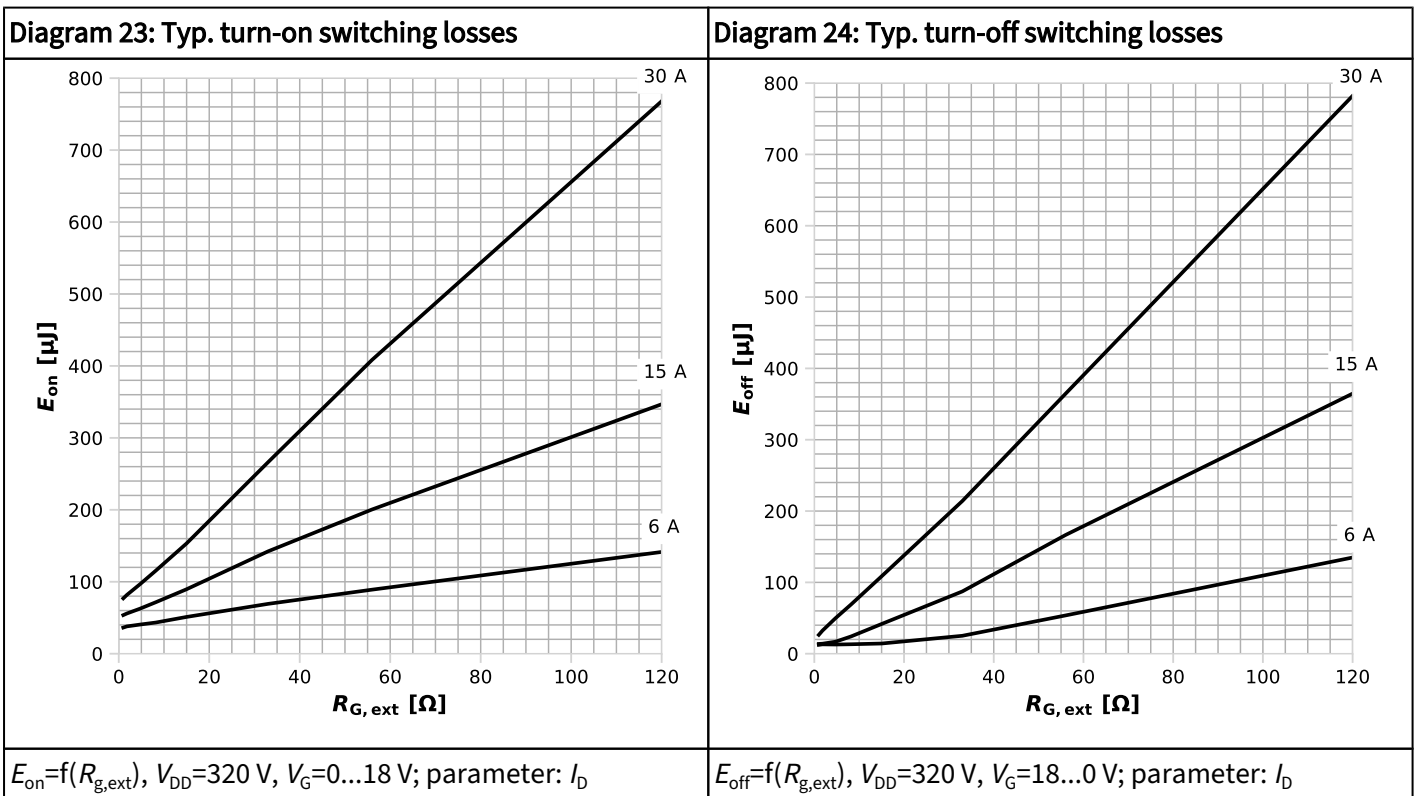
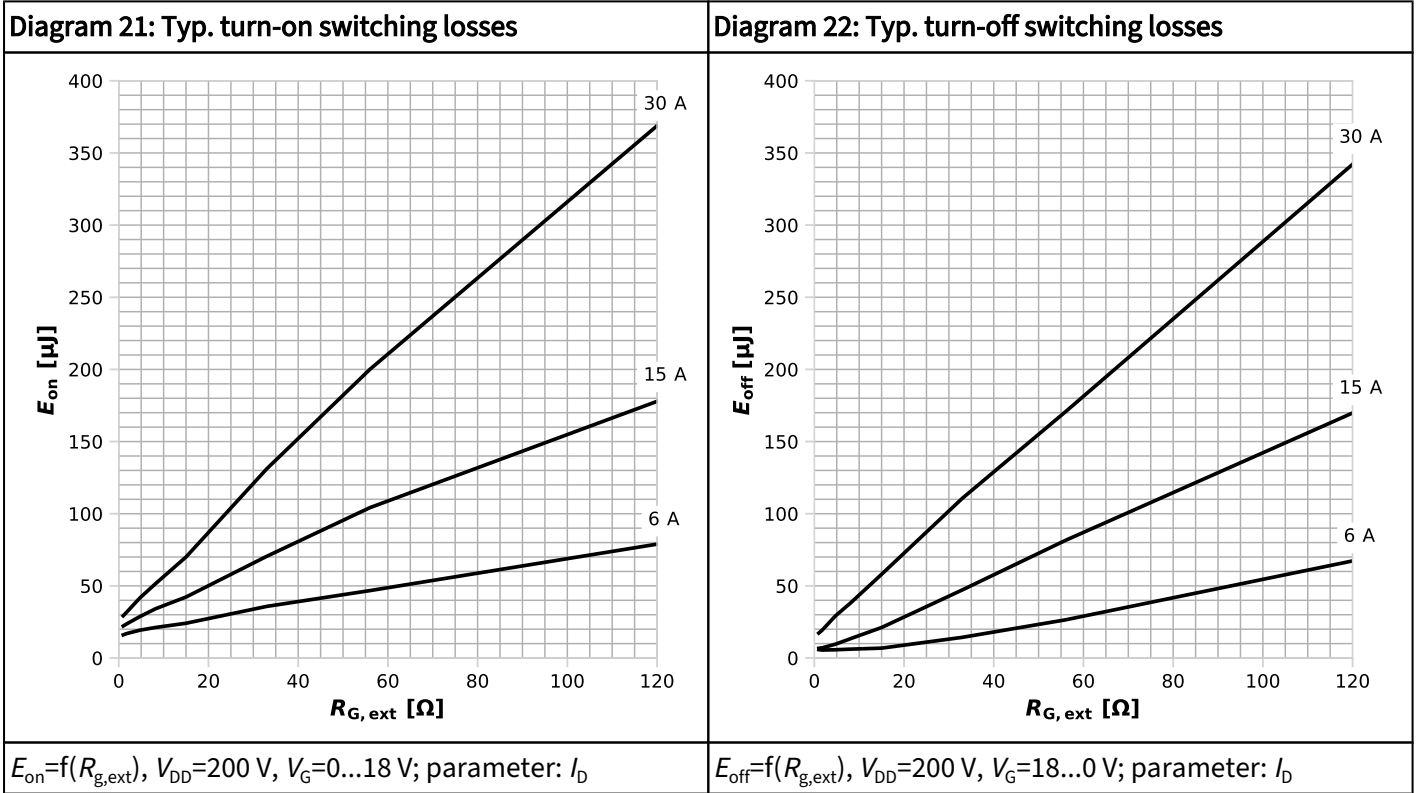
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Diagram 16: Typ. gate charge



$V_{GS} = f(Q_{gate}), V_{DD} = 200 \text{ V}, I_D = 15.7 \text{ A pulsed}, T_j = 25 \text{ }^\circ\text{C}$





6 Test Circuits

Table 9 Switching times (CoolSiC)

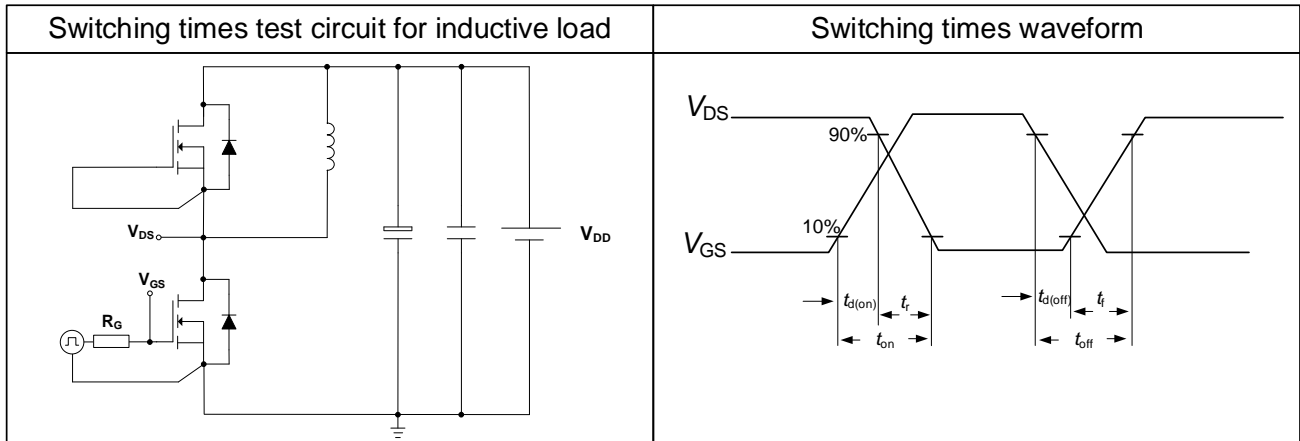
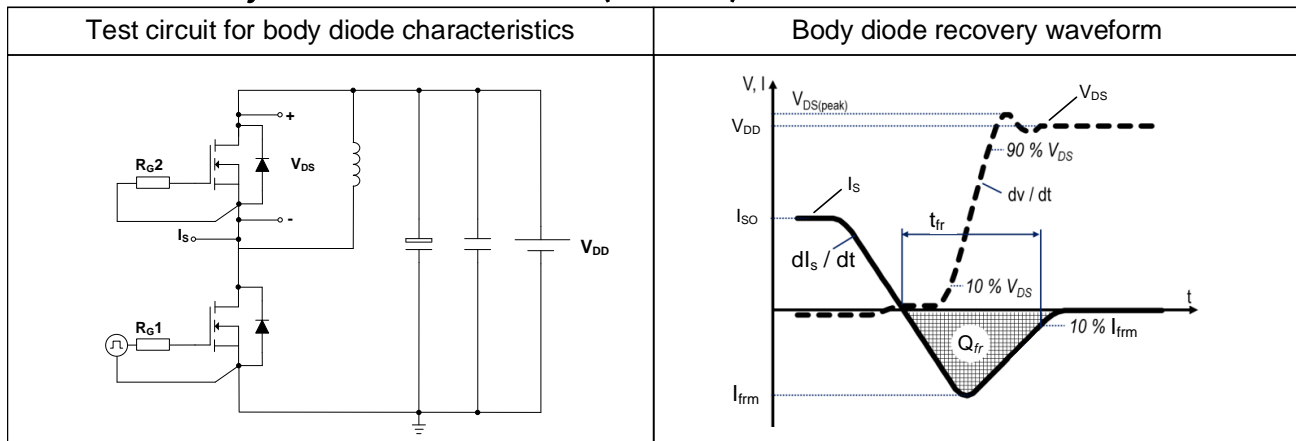
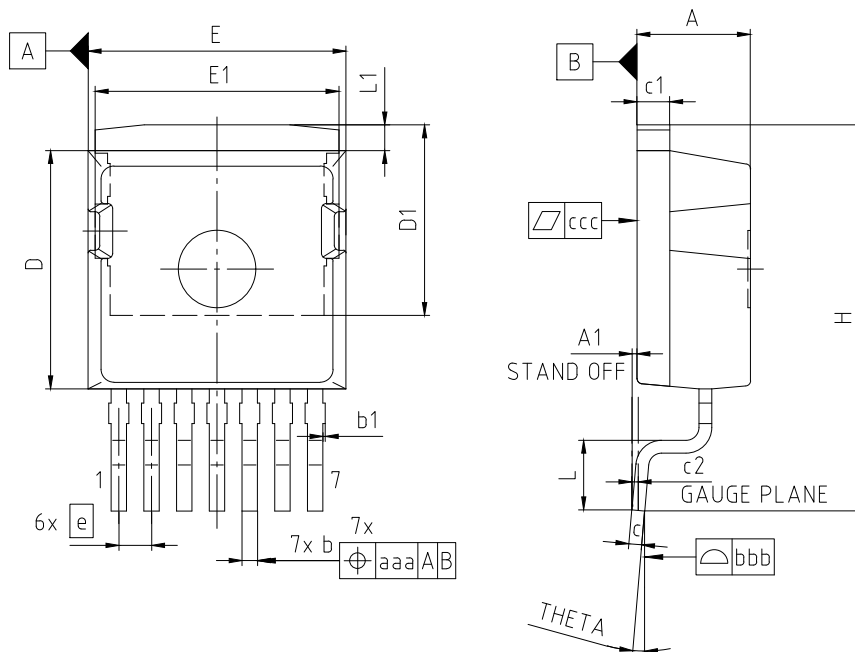


Table 10 Body diode characteristics (CoolSiC)



7 Package Outlines



NOTES:
 ALL METAL SURFACES TIN PLATED EXCEPT AREA OF CUT

PACKAGE - GROUP NUMBER: PG-T0263-7-U04		MILLIMETERS		MILLIMETERS	
DIMENSIONS	MIN.	MAX.	DIMENSIONS	MIN.	MAX.
A	4.30	4.50	E1	9.46	
A1	0.00	0.10	e	1.27	
b	0.50	0.70	N	7	
b1	0.00	0.15	H	15.00	
c	0.40	0.60	L	2.50	2.90
c1	1.17	1.37	L1	0.70	1.30
c2	0.25		THETA	---	8.00°
D	9.05	9.45	aaa	0.25	
D1	7.30	7.50	bbb	0.10	
E	9.80	10.20	ccc	0.05	

Figure 1 Outline PG-T0263-7, dimensions in mm

Revision History

IMBG40R025M2H

Revision 2024-04-27, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.0	2024-04-26	Release of preliminary version
2.0	2024-04-27	Release of final

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